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Kind regards,

Team Nexperia

PDTA123J series

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

Rev. 5 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA123JE	SOT416	SC-75	-	PDTC123JE	ultra small	
PDTA123JM	SOT883	SC-101	-	PDTC123JM	leadless ultra small	
PDTA123JT	SOT23	-	TO-236AB	PDTC123JT	small	
PDTA123JU	SOT323	SC-70	-	PDTC123JU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



2. Pinning information

Table 3. **Pinning** Pin Simplified outline **Graphic symbol Description** SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 2 006aaa144 sym003 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTA123JE	SC-75	plastic surface-mounted package; 3 leads	SOT416			
PDTA123JM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTA123JT	-	plastic surface-mounted package; 3 leads	SOT23			
PDTA123JU	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTA123JE	27
PDTA123JM	DG
PDTA123JT	*23
PDTA123JU	*43

^{[1] * =} placeholder for manufacturing site code.

5. Limiting values

Table 6. Limiting values

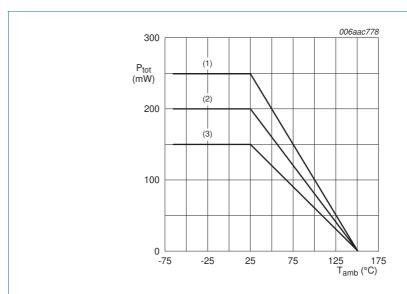
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+5	V
	negative		-	-12	V
Io	output current		-	-100	mA
I_{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA123JE (SOT416)		[1][2] -	150	mW
	PDTA123JM (SOT883)		[2][3]	250	mW
	PDTA123JT (SOT23)		<u>[1]</u> -	250	mW
	PDTA123JU (SOT323)		<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

 $[\]begin{tabular}{ll} [2] & Reflow soldering is the only recommended soldering method. \end{tabular}$

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

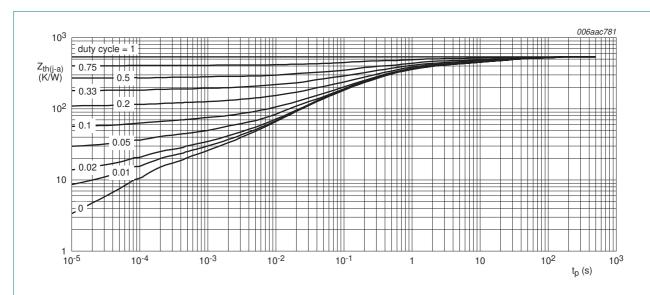
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

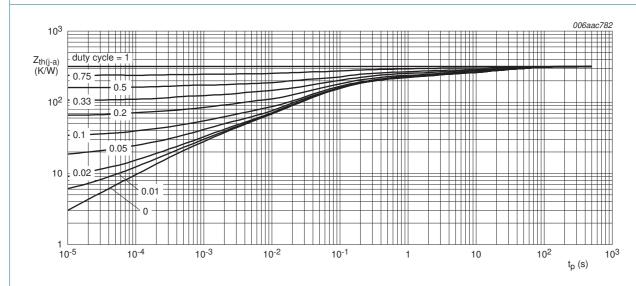
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	in free air				
	PDTA123JE (SOT416)		[1][2]	-	830	K/W
	PDTA123JM (SOT883)		[2][3]	-	500	K/W
	PDTA123JT (SOT23)		[1] -	-	500	K/W
	PDTA123JU (SOT323)		[1] -	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



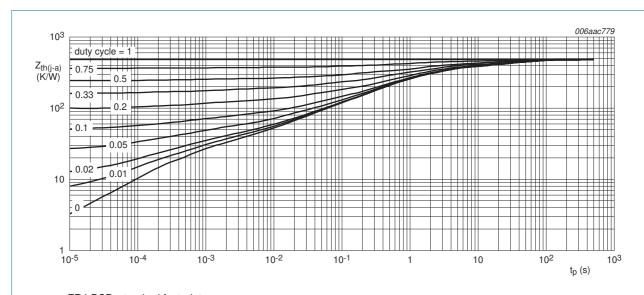
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA123JE (SOT416); typical values



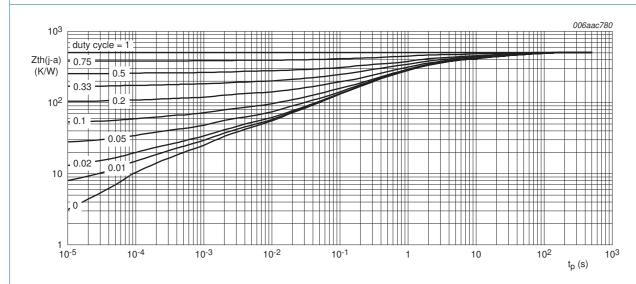
FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA123JM (SOT883); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA123JT (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA123JU (SOT323); typical values

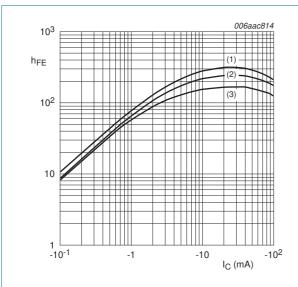
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

arrib -						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	–1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	-180	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.6	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_C = -5 \text{ mA}$	-1.1	-0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C _c	collector capacitance	$\begin{split} V_{CB} = -10 \ V; I_E = I_e = 0 \ A; \\ f = 1 \ MHz \end{split}$	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	1 -	180	-	MHz
						

^[1] Characteristics of built-in transistor.



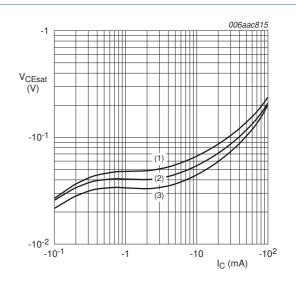
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. DC current gain as a function of collector current; typical values



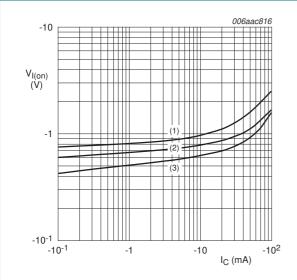
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



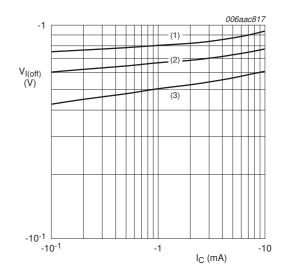
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



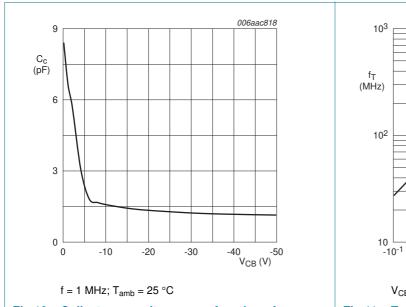
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values



10³

f_T
(MHz)

10²

10₋₁₀-1

-1

-10

I_C (mA)

V_{CE} = -5 V; T_{amb} = 25 °C

Fig 10. Collector capacitance as a function of collector-base voltage; typical values

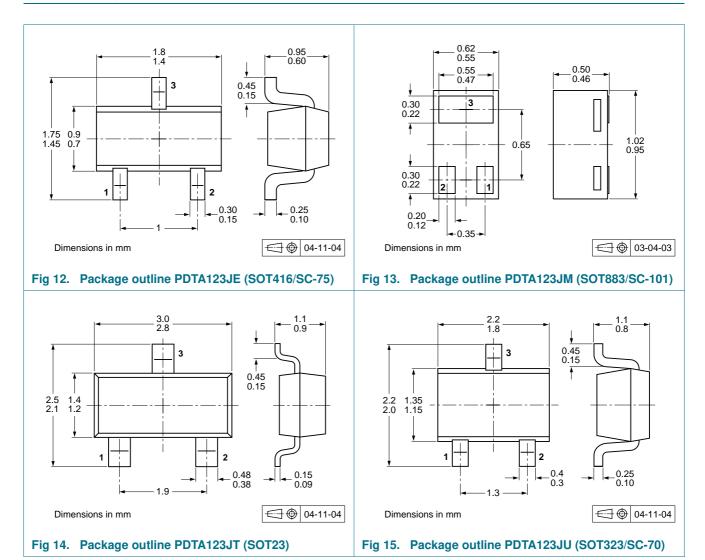
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

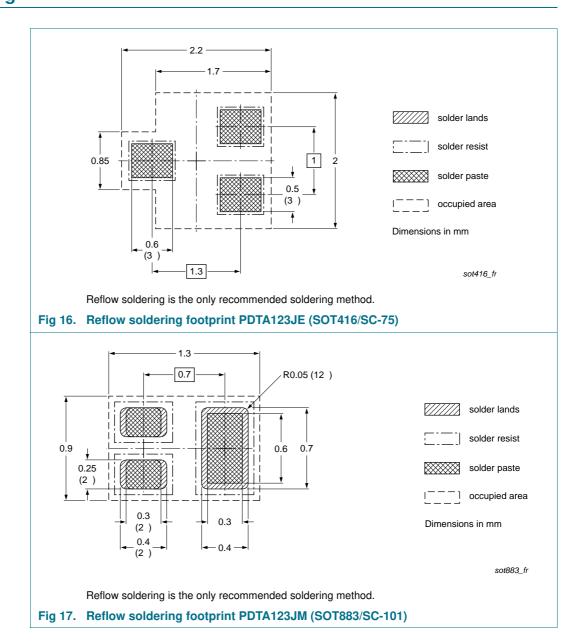
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

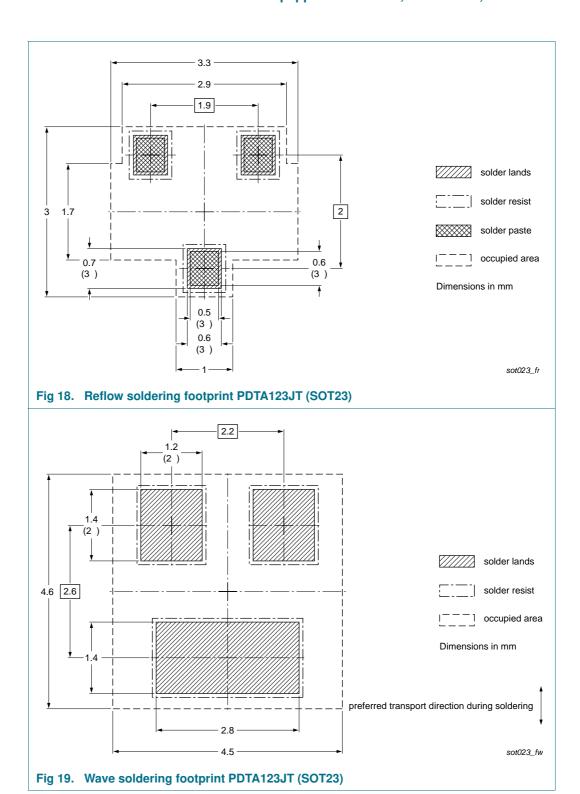
Package Description		Packing	Packing quantity	
		3000	10000	
SOT416	4 mm pitch, 8 mm tape and reel	-115	-135	
SOT883	2 mm pitch, 8 mm tape and reel	-	-315	
SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	
SOT323	4 mm pitch, 8 mm tape and reel	-115	-135	
	SOT416 SOT883 SOT23	SOT416 4 mm pitch, 8 mm tape and reel SOT883 2 mm pitch, 8 mm tape and reel SOT23 4 mm pitch, 8 mm tape and reel	SOT416 4 mm pitch, 8 mm tape and reel -115 SOT883 2 mm pitch, 8 mm tape and reel - SOT23 4 mm pitch, 8 mm tape and reel -215	

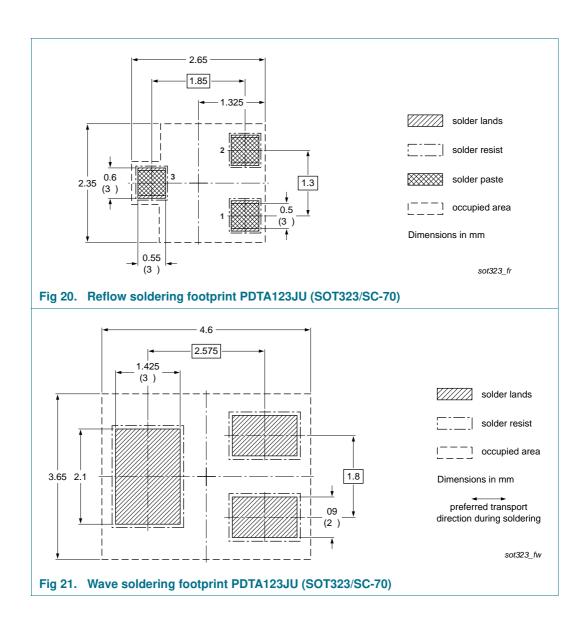
^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

PDTA123J_SER

11. Soldering







12. Revision history

Table 10. Revision history

	-					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PDTA123J_SER v.5	20111221	Product data sheet	-	PDTA123J_SERIES v.4		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 					
	 Type numbers PDTA123JEF, PDTA123JK and PDTA123JS removed 					
	 Section 1 "Pro 	oduct profile": amended				
	 Figure 1 to 11 	Figure 1 to 11: added				
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated and f_T added 					
	 Figure 12, 13, 14 and 15: superseded by minimized package outline drawings 					
	Section 8 "Test information": added					
	 <u>Section 10 "Packing information"</u>: added <u>Section 11 "Soldering"</u>: added 					
	Section 13 "Le	egal information": updated				
PDTA123J_SERIES v.4	20040802	Product data sheet	-	PDTA123J_SERIES v.3		
PDTA123J_SERIES v.3	20030414	Product specification	-	-		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PDTA123J_SER

PDTA123J series

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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PDTA123J series

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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